

## Next Event 2016 Spring Meeting

The 2016 E-MRS Spring Meeting and Exhibit will be held in Lille Grand Palais, from May 2 to 6.



### SEMICONDUCTORS

- K** Group IV semiconductors materials research - growth, characterization and applications to electronics and spintronics
- L** Wide bandgap materials for electron devices
- M** Silicon compatible materials and integrated devices for photonics and optical sensing
- N** Materials frontier for transparent advanced electronics II (*E-MRS / MRS-J bilateral symposium*)
- O** Group IV semiconductors at the nanoscale - applications towards photonics, electronics and life sciences

#### **Hot topics to be covered by the symposium**

- SiC homoepitaxy on low-offcut substrates.
- III-N on silicon : nucleation layer, interface control.
- Thermal issues in GaN and oxide devices.
- Integrating Graphene with Nitrides or SiC (direct growth, layer transfer).
- Selective area growth for new device architectures.
- Wide-bandgap materials for high performance power inverters
- Wide-bandgap materials for MEMS and NEMS
- p-type doping by implantation

**Spring meeting**

**Symposium L**

**Deadline for abstract submission**

**January 15, 2016**

[www.european-mrs.com](http://www.european-mrs.com)

May 2-6, 2016  
Lille Grand Palais



#### Tentative list of invited speakers

GaN on silicon field effect transistors: from growth to electrical properties.

-Andrei Vescan (RWTH Aachen University, Germany)

Thermal issues in GaN devices: challenges and solutions.

-Martin Kuball (Univ. Bristol, UK)

Challenges of the SiC/Epitaxial Graphene Interface

-Rachel. L. Myers-Ward (NRL, Washington DC USA)

Strain management in heteroepitaxial SiC.

-Francesca Iacopi (Griffith University, Australia)

Advanced nanocharacterization of wide bandgap semiconductors and interfaces with two dimensional materials

-Filippo Giannazzo (CNR, Italy)

Bio applications with 3C-SiC.

-Stephen Sadow (Univ. of South Florida, USA)

Characterization of p-type doped SiC

-Sylvie Contreras (Univ. Montpellier II, France)

Diamond electron devices

-Julien Pernot (Néel Inst. Grenoble, France)

Gallium Oxide materials for electronics

Masataka Higashiwaki (NICT Tokyo Jpn)

Additional invited talks will be selected from the submitted abstracts.

#### Scientific committee

Pr. Daniel Alquier (Univ. Tours, France)

Pr. Enrique Calleja (ISOM, Madrid, Spain)

Dr. Didier Chaussende (CNRS, France)

Pr. Rebecca Cheung (SMC, Edinburgh, Scotland)

Dr. Danilo Crippa (LPE, Italy)

Dr. Yvon Cordier (CRHEA-CNRS, France)

Dr. Gabriel Ferro (Univ. Lyon, France)

Dr. Guy Feuillet (CEA, France)

Pr. Philippe Godignon (CNM, Barcelona, Spain)

Pr. Owen James Guy (Univ. of Swansea, UK)

Pr. Kestutis Jarasiunas (Vilnius University, Lithuania)

Dr. Michael Krieger (Erlangen University, Germany)

Dr. Mike Leszczynski (Unipress, Poland)

Dr. Alfonso Patti (STMicroelectronics, Italy)

Dr. Fabrizio Roccaforte (CNR-IMM, Italy)

Dr. Joachim Würfl (FBH, Germany)

Pr. Rositza Yakimova (Linköping University, Sweden)

Dr. Konstantinos Zekentes (FORTH, Greece)

Dr. Marcin Zielinski (NOVASiC, France)

Mr. Arnaud Yvon (STMicroelectronics, France)

#### Symposium chair

Dr. Yvon Cordier, Pr. Daniel Alquier, Dr. Konstantinos Zekentes